

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No. : **09/807,686**
Applicant : LEYDIER, Robert et al.
Filing Date : 4/30/2002
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Art Unit : 2811
Examiner : CRANE, Sara W.
Docket No. : 76.0531
Customer No. : 41754

Mail Stop Non Fee Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

**REVISED SECTION IN RESPONSE TO NOTICE OF NON-
COMPLIANT AMENDMENT**

Dear Sir:

This is in response to the Notice of Non-Compliant Amendment mailed on May 5, 2006. Applicants herein correct the listing of the claims as required therein.

Amendments to the Claims begin on page 2 of this paper

Respectfully Submitted,
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Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A chip for a chip-containing portable article, ~~in particular an article of card format~~ the chip comprising a silicon substrate layer ~~whose~~ having an active face ~~has~~ with circuits integrated therein defining a central processor unit and memories, and an additional layer of silicon that is sealed to the active face of the silicon substrate layer by a sealing layer, the additional layer of silicon covering at least part of said active face, the additional layer of silicon ~~and comprising~~ physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm .
2. (withdrawn) A chip according to Claim 1, wherein the physical means are means providing physical protection against the action of electromagnetic radiation in the infrared range.
3. (withdrawn) A chip according to Claim 2, wherein the physical means are means providing physical protection against the action of electromagnetic radiation in the ultraviolet, visible, and infrared ranges.
4. (cancelled)
5. (previously presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are silicon dopants.
6. (previously presented) A chip according to Claim 5, wherein the concentration of silicon dopants lies in the range 10^{17} to 10^{20} atoms per cm^3 .
7. (previously presented) A chip according to Claim 5, wherein the silicon dopants are phosphorus or boron.

8. (cancelled)
9. (cancelled)
10. (previously presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by surface irregularities.
11. (cancelled)
12. (currently amended) A chip according to claim 10, wherein the surfaces irregularities are provided in the ~~bottom~~ face of the additional layer of silicon that is in contact with the sealing layer.
13. (currently amended) A chip according to Claim 10, wherein the surface irregularities are provided in the ~~top~~ face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.
14. (currently amended) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by at least one ~~layer~~ deposition of metal on the additional layer of silicon.
15. (currently amended) A chip according to Claim 14, wherein the metal deposition ~~layer~~ has a thickness greater than 50 Å.
16. (currently amended) A chip according to Claim 14, wherein the metal deposition is ~~placed~~ on the ~~bottom~~ face of the additional ~~layer~~ of silicon that is in contact with the sealing layer.
17. (currently amended) A chip according to Claim 14, wherein the metal layer deposition is ~~placed~~ on the ~~top~~ face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.
18. (cancelled)
19. (currently amended) A chip according to Claim 16, wherein the metal layer deposition has a thickness of about 100 Å.

20.(new) A portable article provided with a chip that comprises a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories, the chip further comprising an additional layer of silicon that is sealed to the active face of the silicon substrate layer by a sealing layer, the additional layer of silicon covering at least part of said active face, the additional layer of silicon comprising physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm .